

Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25^\circ C$; non-repetitive, off-state; FIG.7)	V_{pp}	2.5	kV

($T_j=25^\circ C$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V R_L=33$	- -	MAX.	50	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ C$ $R_L=3.3K$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	50	mA
				90	
I_H	$I_T=100mA$		MAX.	50	mA
dV/dt	$V_D=400V$ Gate Open $T_j=125^\circ C$		MIN.	2000	V/ μ s
$(dI/dt)c$	$(dV/dt)c=20V/\mu s, T_j=125^\circ C$		MIN.	12	A/ms
t_{on}	$I_G=80mA I_A=400mA I_R=40mA$ $T_j=25^\circ C$	TYP.		5	μ s
				50	

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=11A t_p=380\mu s$	$T_j=25^\circ C$	1.5	V
V_{TO}	Threshold voltage	$T_j=125^\circ C$	0.8	V
R_D	Dynamic resistance	$T_j=125^\circ C$	44	m
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ C$	5	μA
I_{RRM}		$T_j=125^\circ C$	0.25	mA

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	2.5	/W
$R_{th(j-a)}$	junction to ambient (AC)	60	/W

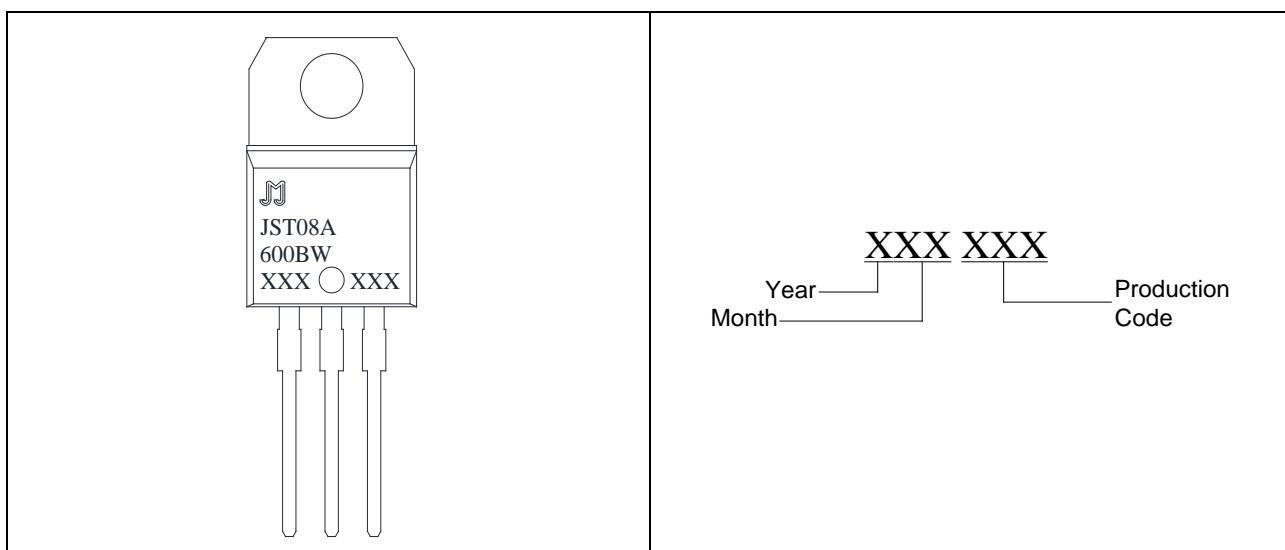
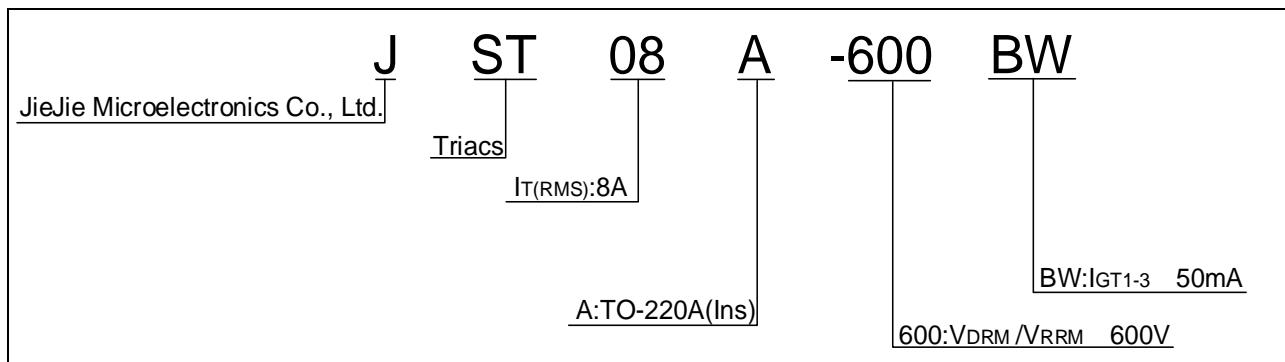
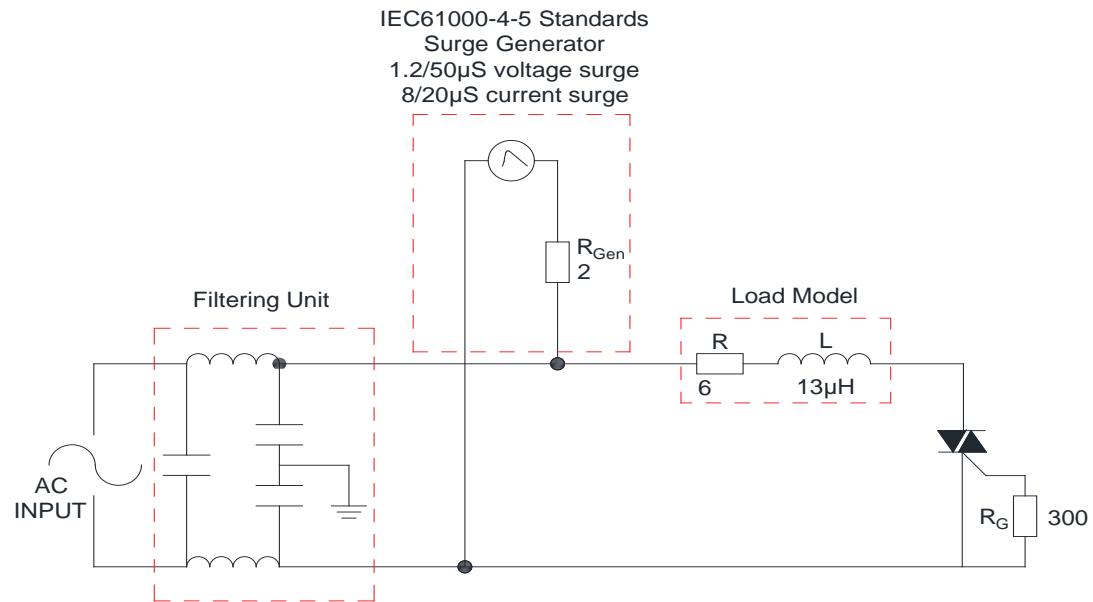


FIG.1 Maximum power dissipation versus RMS on-state current



FIG.2: RMS on-state current versus case temperature

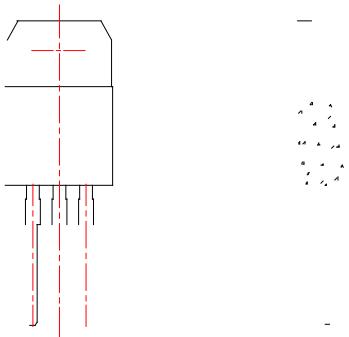
FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
JST08A-600BW	600	50	TO-220A(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Apr.11, 2023	A.1.0	Last updated



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